



Features:

- Ideal for 500 – 4000 MHz High Linearity / High Dynamic Range Applications
- Excellent RF Performance:
 - 44 dBm OIP3
 - 25 dBm P1dB
 - 11 dB Gain @ 500 - 4000 MHz
 - 3 dB NF @ 900- 2700 MHz
- Single +7.5V Supply
- MTTF > 100 years @ 85°C ambient temperature

Description:

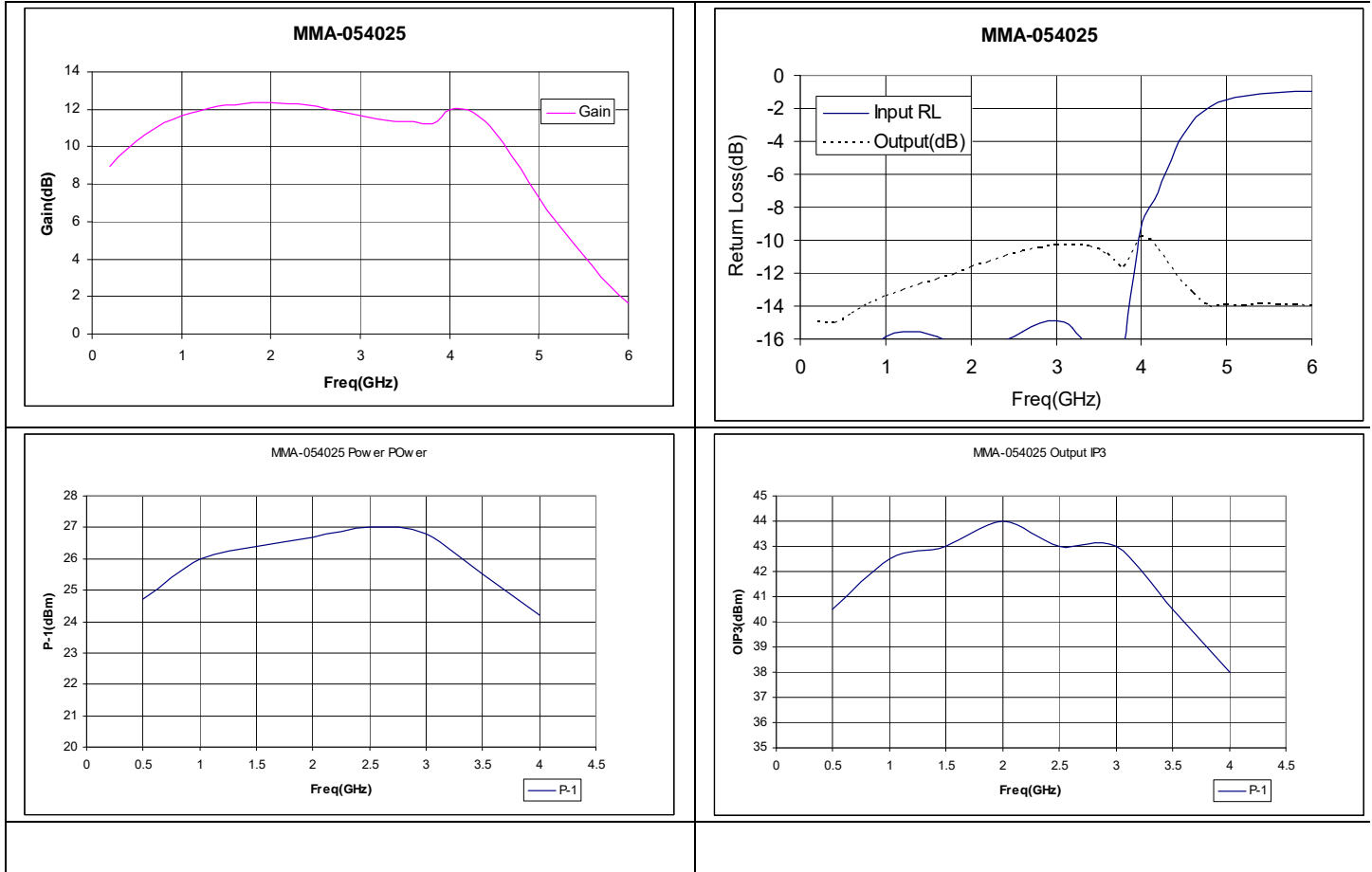
The MMA-054025 is a high linearity broadband MMIC die amplifier. This MMIC is ideally suited for high linearity driver and high dynamic range LNA applications. The applications include 2G, 2.5G, and 3G wireless infrastructure standards, such as GSM, TDMA, CDMA, EDGE, CDMA2000, WCDMA, TD-SCDMA, and UMTS base stations. The third order intercept point performance is excellent, typically 18 dB above the 1 dB gain compression point.

Electrical Specifications: @ $V_{ds}=7.5V$, $I_{ds}=300mA$, $T_a=25\text{ }^\circ\text{C}$ $Z_0=50\text{ ohm}$

Parameter	Units	Typical Data
Frequency Range	MHz	500-4000
Gain(Typ / Min)	dB	11
Gain Flatness(Typ / Min)	+/-dB	1.0
Input Return Loss(Typ)	dB	10
Output Return Loss(Typ)	dB	10
Output P1dB(Typ)	dBm	25
Output IP3(Typ / Min) ⁽¹⁾	dBm	44
Noise Figure	dB	3.5
Operating Current Range(Min / Max)	mA	300 / 350
Thermal Resistance(Typ)	°C /W	25

(1) Output IP3 is measured with two tones at output power of 11 dBm/tone separated by 10 MHz

Typical RF Performance: $V_{ds}=7.5V$, $I_{ds}=300mA$, $T_a=25\text{ }^\circ C$ 50 Ohm system





Typical Scattering Parameters:

(V_{ds}=7.5V, I_{ds}=300mA, T_a=25°C Reference Planes at Leads)

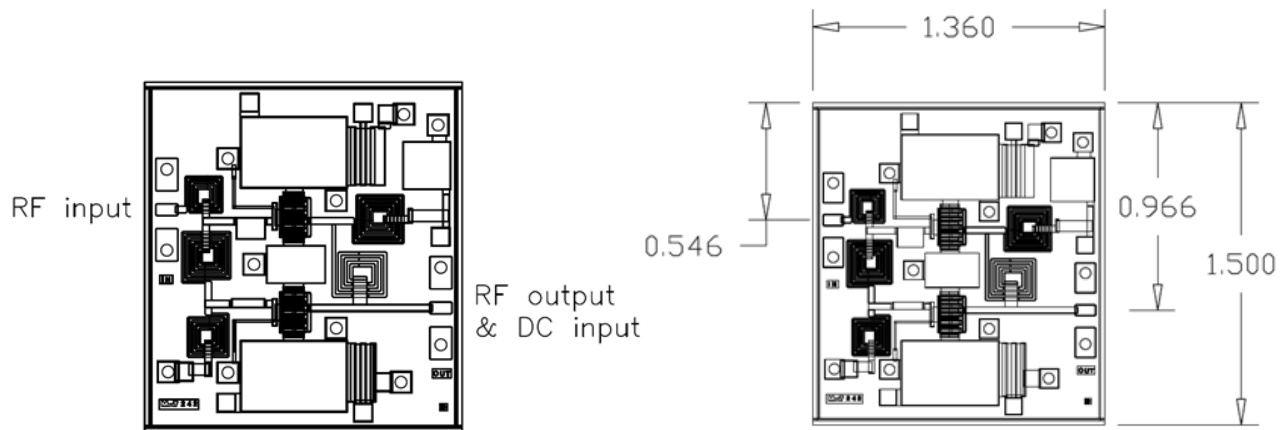
Freq (GHz)	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
0.2	0.06	12.2	2.80	175.8	0.006	71.4	0.18	-93.0
0.4	0.10	-0.3	3.12	160.2	0.011	48.5	0.18	-125.8
0.6	0.13	-21.9	3.42	142.5	0.016	29.2	0.19	-150.4
0.8	0.15	-45.6	3.65	123.5	0.019	13.1	0.20	-170.6
1.0	0.16	-69.9	3.82	104.7	0.023	-2.4	0.21	171.6
1.2	0.17	-95.3	3.95	85.3	0.027	-18.6	0.22	156.2
1.4	0.17	-122.1	4.05	66.3	0.030	-34.2	0.23	141.1
1.6	0.16	-151.0	4.09	47.0	0.034	-50.3	0.24	126.1
1.8	0.15	178.4	4.14	27.7	0.037	-66.5	0.25	112.0
2.0	0.15	144.9	4.15	8.3	0.040	-82.7	0.26	96.8
2.2	0.15	110.3	4.13	-11.2	0.043	-99.3	0.27	82.0
2.4	0.16	75.5	4.08	-30.6	0.046	-115.9	0.28	66.0
2.6	0.17	43.1	4.01	-49.6	0.048	-131.9	0.29	50.4
2.8	0.18	13.0	3.92	-68.5	0.050	-147.8	0.30	34.3
3.0	0.18	-13.5	3.83	-87.0	0.053	-163.0	0.30	18.6
3.2	0.17	-37.7	3.75	-105.1	0.056	-178.3	0.31	2.4
3.4	0.14	-56.1	3.71	-123.1	0.059	167.7	0.30	-12.8
3.6	0.09	-55.6	3.69	-141.7	0.067	154.6	0.29	-28.4
3.8	0.15	-3.6	3.65	-159.6	0.091	137.7	0.26	-36.5
4.0	0.35	-41.5	3.97	-179.7	0.101	94.4	0.33	-50.3
4.2	0.44	-63.4	3.96	154.3	0.085	69.8	0.30	-72.4
4.4	0.59	-87.7	3.70	128.6	0.078	48.0	0.25	-86.7
4.6	0.72	-115.7	3.24	104.2	0.069	26.2	0.22	-94.4
4.8	0.80	-143.4	2.76	82.6	0.060	5.5	0.20	-99.5
5.0	0.85	-168.5	2.33	63.7	0.052	-12.0	0.20	-105.4
5.2	0.87	168.1	1.99	46.4	0.045	-28.7	0.20	-113.3
5.4	0.88	147.4	1.72	30.8	0.040	-43.0	0.20	-122.7
5.6	0.89	127.6	1.52	15.7	0.036	-57.4	0.20	-132.8
5.8	0.89	109.7	1.34	0.9	0.033	-71.0	0.20	-144.0
6.0	0.90	92.8	1.21	-13.4	0.030	-84.2	0.20	-154.8

Absolute Maximum Ratings: $(T_a = 25\text{ }^\circ\text{C})^*$

SYMBOL	PARAMETERS	UNITS	ABSOLUTE MAXIMUM
Vds	Drain-Source Voltage	V	8.5
I _{ds}	Drain Current	mA	400
I _{gs}	Gate Current	mA	3
P _{diss}	DC Power Dissipation	W	3.2
P _{in max}	RF Input Power	dBm	+24
T _{oper}	Operating Temperature	°C	-40 to +85
T _{ch}	Channel Temperature	°C	150
T _{stg}	Storage Temperature	°C	-60 to 150

*Operation of this device above any one of these parameters may cause permanent damage.

Outline Drawing:



UNIT: mm

Pad size: 0.1 X0.05 mm